

REMARKS

Applicants will address each of the Examiner's rejections in the order in which they appear in the Final Rejection.

Claim Rejections - 35 USC §102

In the Final Rejection, the Examiner rejects Claims 43-45 and 49-51 under 35 USC §102(e) as being anticipated by Balasubramanyam et al. This rejection is respectfully traversed.

More specifically, independent Claims 43 and 49 each recite that a bottom surface of the first conductive layer is in contact with the gate insulating film.

The Examiner contends that Balasubramanyam teaches a gate electrode 22, 24 adjacent to the gate oxide 18 with a gate insulating layer 20 interposed therebetween. The Examiner further contends that the gate electrode has a first conductive layer 22 comprising tungsten/nitride and a second conductive layer 24 comprising tungsten on the first conductive layer. The Examiner then contends that the reference discloses the first conductive layer 22 being in contact with the gate insulating layer 20.

Applicants respectfully disagree. Balasubramanyam describes layer 20 as a doped polysilicon layer (see col. 5, lns. 34-36). Hence, layer 20 is not the gate insulating layer, and Balasubramanyam does not disclose or suggest the claimed limitation that a bottom surface of the first conductive layer is in contact with the gate insulating film. Accordingly, it is respectfully requested that this rejection be withdrawn.

Claim Rejections - 35 USC §103

The Examiner also rejects Claims 46-48, 52-54, and 79-102 under 35 §USC 103(a) as being unpatentable over Balasubramanyam et al. in view of Seo et al. This rejection is also respectfully traversed.

Independent Claims 79, 85, 91, 97 each recite that a bottom surface of the first conductive layer is in contact with the gate insulating film. As explained above, Balasubramanyam does not disclose or suggest this feature.

Seo also fails to disclose or suggest this feature. Assuming for the sake of argument that 2a or 2b in Seo is a first conductive layer, Seo does not disclose the bottom surface of the first conductive layer in contact with the gate insulating film. Instead, layers 2a and 2b are in contact with the insulating substrate 1.

Hence, the cited references fail to disclose or suggest the claimed invention. Accordingly, it is request that this rejection be withdrawn.

New Claims and Amendments To Claims

Applicants are adding new Claims 103-114 herewith. These new claims include the feature that a side surface of the first conductive layer is aligned with a side surface of the second conductive layer. Please charge our deposit account 50/1039 for any fee due for these new claims.

In order to better claim the present invention, Applicants have also amended each of the independent claims to recite that the bottom surface of the first conductive layer is larger than a bottom surface of the second conductive layer.

Each of these limitations is supported by, for example, Fig. 15B of the present application, and it is requested that these new claims and amendments now be entered.

Conclusion

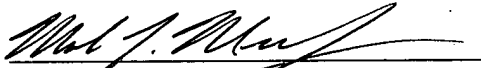
For at least the above-stated reasons, the claims of the present application are patentable over the cited references and should be allowed.

If any further fee should be due for this amendment, please charge our deposit account 50/1039.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

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